





20V PNP HIGH GAIN TRANSISTOR IN SOT89

Features

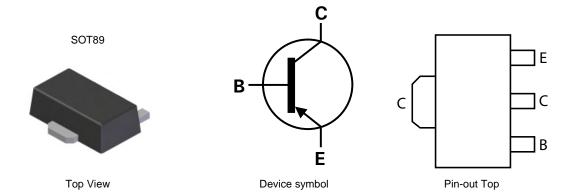
- BV_{CEO} > -20V
- High current capability Max Continuous Current I_C = -6A
- Low saturation voltage V_{CE(sat)} < -47mV @ I_C = -1A
- R_{CE(sat)} = 28mΩ
- P_D = 2.4W
- Complementary part number ZXTN19020DZ
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Moisture Sensitivity: Level 1 per J-STD-020
- UL Flammability Rating 94V-0
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (Approximate)

Application

- Power disconnect switch
- Battery chargers
- High side drivers
- Motor drive



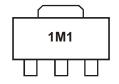
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19020DZTA	1M1	7 12		1,000

Notes:

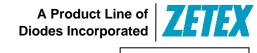
- 1. No purposefully added lead.
- 2. Halogen and Antimony Free. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com
- 3. For packaging details, go to our website at http://www.diodes.com

Marking Information



1M1 = Product Type Marking Code





ZXTP19020DZ

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{ECO}	-4	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current (Note 6)	I _C	-6	A
Base current	I _B	-1	A
Peak Pulse Current	I _{CM}	-15	A

Thermal Characteristics @TA = 25°C unless otherwise specified

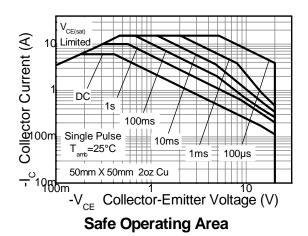
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	D-	1.1	W
Linear derating factor	P _D	8.8	mW/°C
Power Dissipation (Note 5)	PD	1.8	W
Linear derating factor	Fβ	14.4	mW/°C
Power Dissipation (Note 6)	P _D	2.4	W
Linear derating factor	Fβ	19.2	mW/°C
Power Dissipation (Note 7)	PD	4.46	W
Linear derating factor	Fβ	35.7	mW/°C
Power Dissipation (Note 8)	PD	26.7	W
Linear derating factor	Fβ	213	mW/°C
Thermal Resistance, Junction to Ambient (Note 4)	$R_{ heta JA}$	117	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	68	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	51	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ heta JA}$	117	°C/W
Thermal Resistance, Junction to Leads (Note 8)	$R_{ heta JL}$	4.69	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

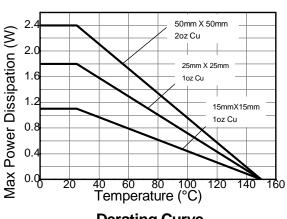
Notes:

- 4. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

 5. Mounted on 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions. 7. As note 6 above measured at t<5 seconds.
- 8. Junction to case (collector tab). Typical

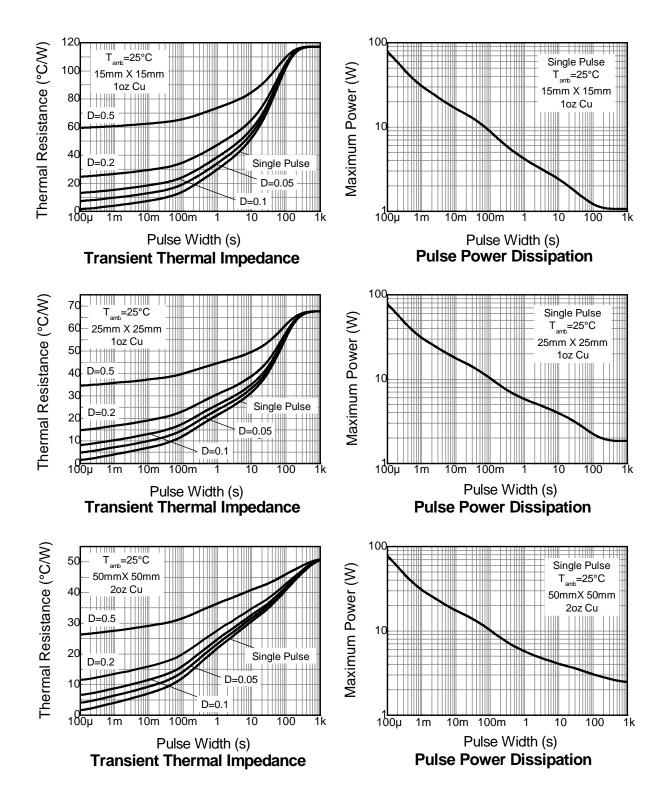
Thermal Characteristics







Thermal Characteristics (- Continued)







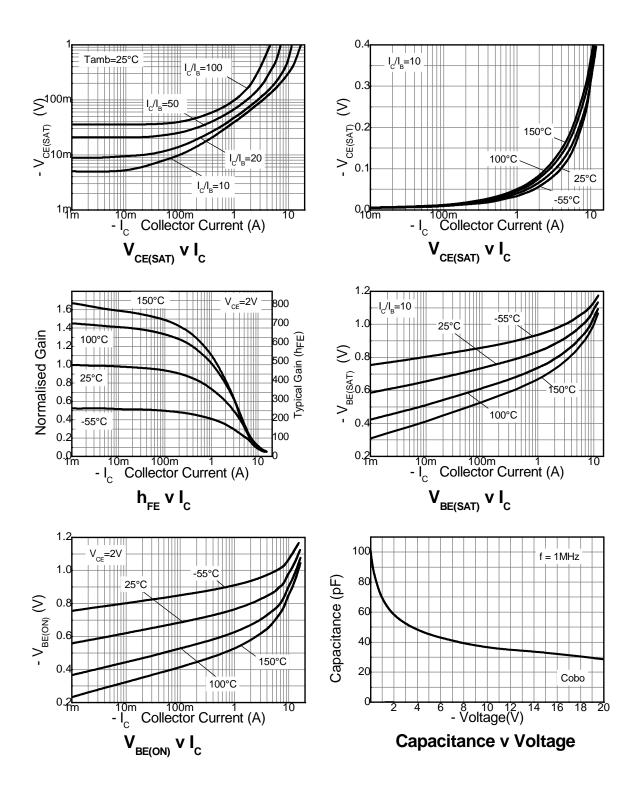
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-25	-55	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Notes 9)	BV _{CEO}	-20	-50	-	V	$I_C = -10mA$
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECX}	-4	-8.6	-	V	I_E = -100μA, R_{BC} < 1k Ω or 0.25V > V_{BC} > -0.25V
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECO}	-4	-8.6	-	V	I _E = -100μA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.2	-	V	$I_E = -100 \mu A$
Collector Cutoff Current		-	< -1	-50	nA	V _{CB} = -25V
Collector Cutoff Current	Ісво	-	-	-500		$V_{CB} = -25V, T_A = 100^{\circ}C$
Emitter Cutoff Current	I _{EBO}	-	< -1	-50	nA	$V_{EB} = -5.6V$
		300	450	900		$I_C = -100 \text{mA}, V_{CE} = -2 \text{V}$
DC current transfer Static ratio (Notes 9)	h	200	290	-	-	$I_C = -2A$, $V_{CE} = -2V$
De current transfer Static ratio (Notes 9)	h _{FE}	65	110	-		$I_C = -6A$, $V_{CE} = -2V$
		-	25	-		$I_C = -15A$, $V_{CE} = -2V$
		-	-40	-47	mV	$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage (Notes 9)	V	-	-100	-130		$I_C = -1A$, $I_B = -10mA$
Collector-Efflitter Saturation Voltage (Notes 9)	$V_{CE(sat)}$	-	-115	-145		$I_C = -2A$, $I_B = -40mA$
		-	-225	-275		$I_C = -6A$, $I_B = -300mA$
Base-Emitter Saturation Voltage (Notes 9)	$V_{BE(sat)}$	-	-1000	-1100	mV	$I_C = -6A$, $I_B = -300$ mA
Base-Emitter Turn-on Voltage (Notes 9)	$V_{BE(on)}$	-	-865	-1000	mV	$I_C = -6A$, $V_{CE} = -2V$
Transitional Frequency (Notes 9)	f_T	-	176	-	MHz	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz
Input Capacitance	C _{ibo}	-	-	400	pF	$V_{EB} = -0.5V, f = 1MHz$
Output capacitance	C_{obo}	-	36	45	pF	$V_{CB} = -10V$, $f = 1MHz$
Delay time	t _d	-	23	-	ns	
Rise time	t _r	-	18.4	-	ns	$V_{CC} = -10V, I_{C} = -1A,$
Storage time	ts	-	266	-	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall time	t _f	-	49.6	-	ns	

Notes: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

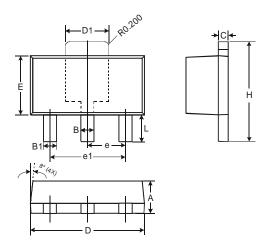


Typical Electrical Characteristics



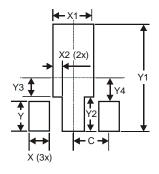


Package Outline Dimensions



SOT89			
Dim	Min	Max	
Α	1.40	1.60	
В	0.44	0.62	
B1	0.35	0.54	
С	0.35	0.43	
D	4.40	4.60	
D1	1.52	1.83	
Е	2.29	2.60	
е	1.50 Typ		
e1	3.00 Typ		
Η	3.94	4.25	
١	0.89	1.20	
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1 500





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